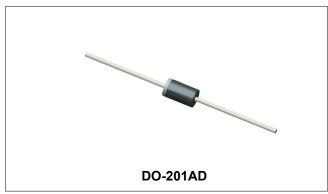






1N5400 THRU 1N5408 GLASS PASSIVATED SILICON RECTIFIER



Features

- The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- Construction utilizes void-free molded plastic technique
- Low reverse leakage
- High forward surge current capability
- High temperature soldering guaranteed:
 250° C/10s,0.375" (9.5mm) lead length,5lbs.(2.3kg) tension
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Mechanical Data

- Case: DO-201AD molded plastic body
- Terminals: Plated axial leads, solderable per MIL-STD-750, Method 2026
- . Polarity: Color band denotes cathode end
- Mounting Position: Any
- Weight: 0.04 ounce, 1.10 grams

Maximum Ratings and Electrical Characteristics @TA=25°C unless otherwise specified

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

Characteristic	Symbol	1N 5400	1N 5401	1N 5402	1N 5403	1N 5404	1N 5405	1N 5406	1N 5407	1N 5408	Units
Maximum repetitive peak reverse voltage Maximum DC blocking voltage	$V_{RRM} \ V_{DC}$	50	100	200	300	400	500	600	800	1000	V
Maximum RMS voltage	V _{RMS}	35	70	140	210	280	350	420	560	700	V
Maximum average forward rectified current 0.375"(9.5mm) lead length at @T _A =75°C	I _(AV)	3.0			Α						
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	200				Α					
Maximum instantaneous forward voltage at 3.0A	V _F	1.2				V					
Maximum DC reverse current @T _A = 25°C At Rated DC Blocking Voltage @T _A = 100°C	I _R	5.0 100			μΑ						
Typical Junction Capacitance (Note 1)	CJ	30			pF						
Typical Thermal Resistance Junction to Ambient (Note 2)	R _{θJA}	20			°C/W						
Operating junction temperature range	TJ	-65 to +175			°C						
Operating storage temperature range	T _{STG}	-65 to +175			°C						

Note: 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

2. Thermal resistance from junction to ambient at 0.375"(9.5mm)lead length, P.C.B. mounted

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 sales@ smc-diodes.com







Ratings and Characteristics Curves

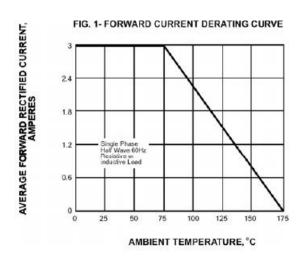


FIG. 3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

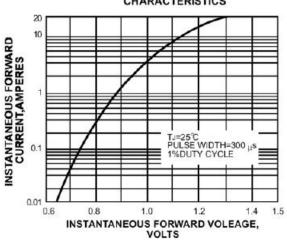
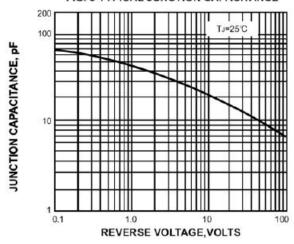
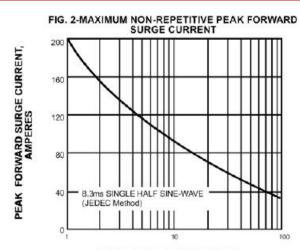
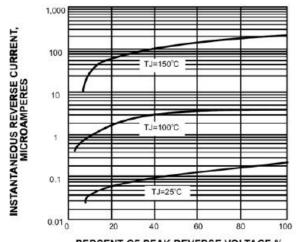


FIG. 5-TYPICAL JUNCTION CAPACITANCE

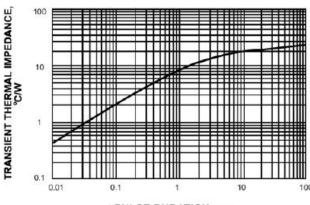




NUMBER OF CYCLES AT 60 Hz FIG. 4-TYPICAL REVERSE CHARACTERISTICS



PERCENT OF PEAK REVERSE VOLTAGE,%
FIG. 6-TYPICAL TRANSIENT THERMAL IMPEDANCE



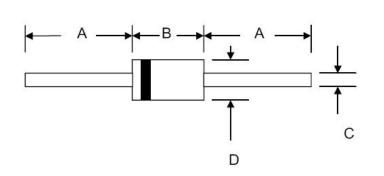
- t,PULSE DURATION,sec.
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Mechanical Dimensions DO-201AD



SYMBOL	Millim	neters	Inches			
OTMIDGE	Min.	Max.	Min.	Max.		
Α	25.4	-	1.000	-		
В	7.2	9.5	0.285	0.375		
С	1.2	1.3	0.048	0.052		
D	5.0	5.6	0.197	0.220		

Ordering Information

Device	Package	Shipping		
1N5400-1N5408	DO-201AD	1250pcs / tape		
1110400-1110406	(Pb-Free)			

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram



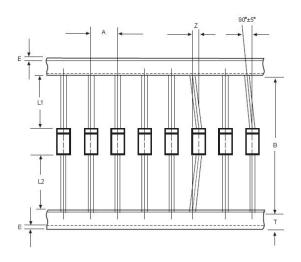
Where XXXXX is YYWWL

1N5400 = Part Name SSG = SSG YY = Year WW = Week

Cautions: Molding resin Epoxy resin UL:94V-0

= Lot Number

Carrier Tape Specification DO-201AD



SYMBOL	Millimeters				
	Min.	Max.			
А	9.50	10.50			
В	50.9	53.9			
Z	-	1.20			
Т	5.60	6.40			
E	-	0.80			
IL1-L2I	-	1.0			

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